



MICRON SEMICONDUCTOR LIMITED

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3366 TAMU
College Station
Texas, TX 77843-3366
United States of America
Attention: Jerry W Deason; Tel: 979-845-1411

7th July 2011

INVOICE NO: 13333
VAT No: GB 376 8710-14

REF: PURCHASE ORDER NO P003844

Supply:-

Quantity 1, **BB1(DS)-300** SILICON DETECTOR
Type 2M in Custom PCB with Readout
Serial No: 2852-14 (290 μ m)

UNIT PRICE: \$5,500

\$5,500

TOTAL INVOICE VALUE: \$5,500

BALANCE OF ORDER: Quantity 1, **BB1(DS)-300** Detector
& NRE (Non-Recurring Engineering)

Detectors sent to: Jerry W Deason

Prices: US Dollars, FOB College Station

US Tariff Code: 8541-10-0080 - DIODE: Other NSPF (Not PHOTSN), Rated: 0%

Payment Terms: Net 30 days

Payment: US\$ cheque to above address OR wire transfer to:

Barclays Bank plc, 139-142 North Street, BRIGHTON, BN1 1RU, UK

Sort Code: 20-12-75; Account No: 82949877

IBAN No: GB90 BARC20127582949877; SWIFT BIC: BARCGB22

Warranty: 12 months manufacturing/specification defects attributed to Micron Semiconductor Limited from INVOICE DATE.

Origin: This detector was manufactured wholly in the UK (EEC) at Micron Semiconductor Works, Lancing, England, UK.

COLIN D WILBURN, DIRECTOR



· Silicon Solid State Detectors ·
Astrophysics · High Energy Physics · Nuclear Physics
Electro Optics · Radioactive Beam Physics

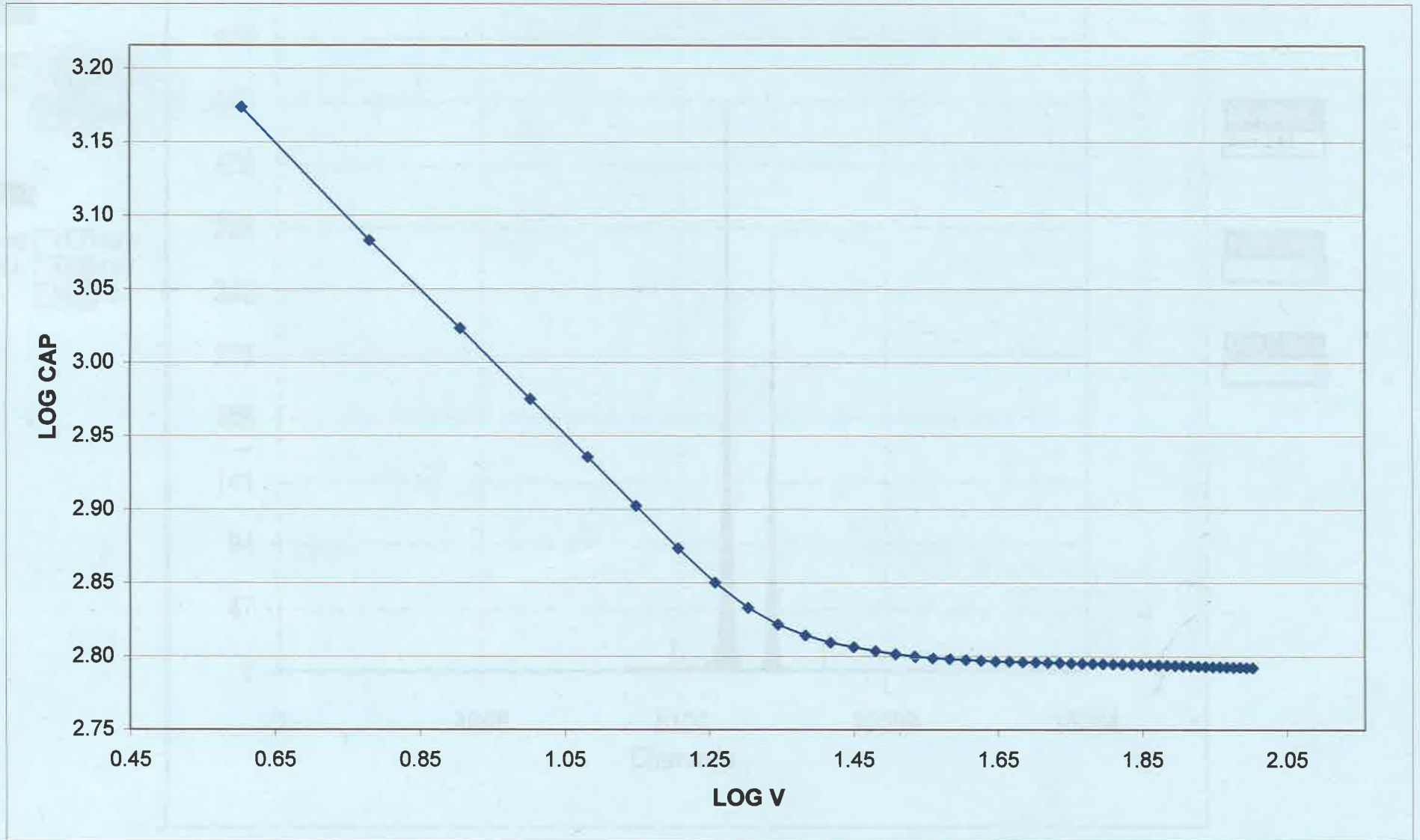
Depletion Plot

BB1-300

Wafer No.: **2852-14**

Thickness: **290** μm

Depletion: **30** Volts



Resolution Plot

DESIGN BB1-300 TYPE 2M

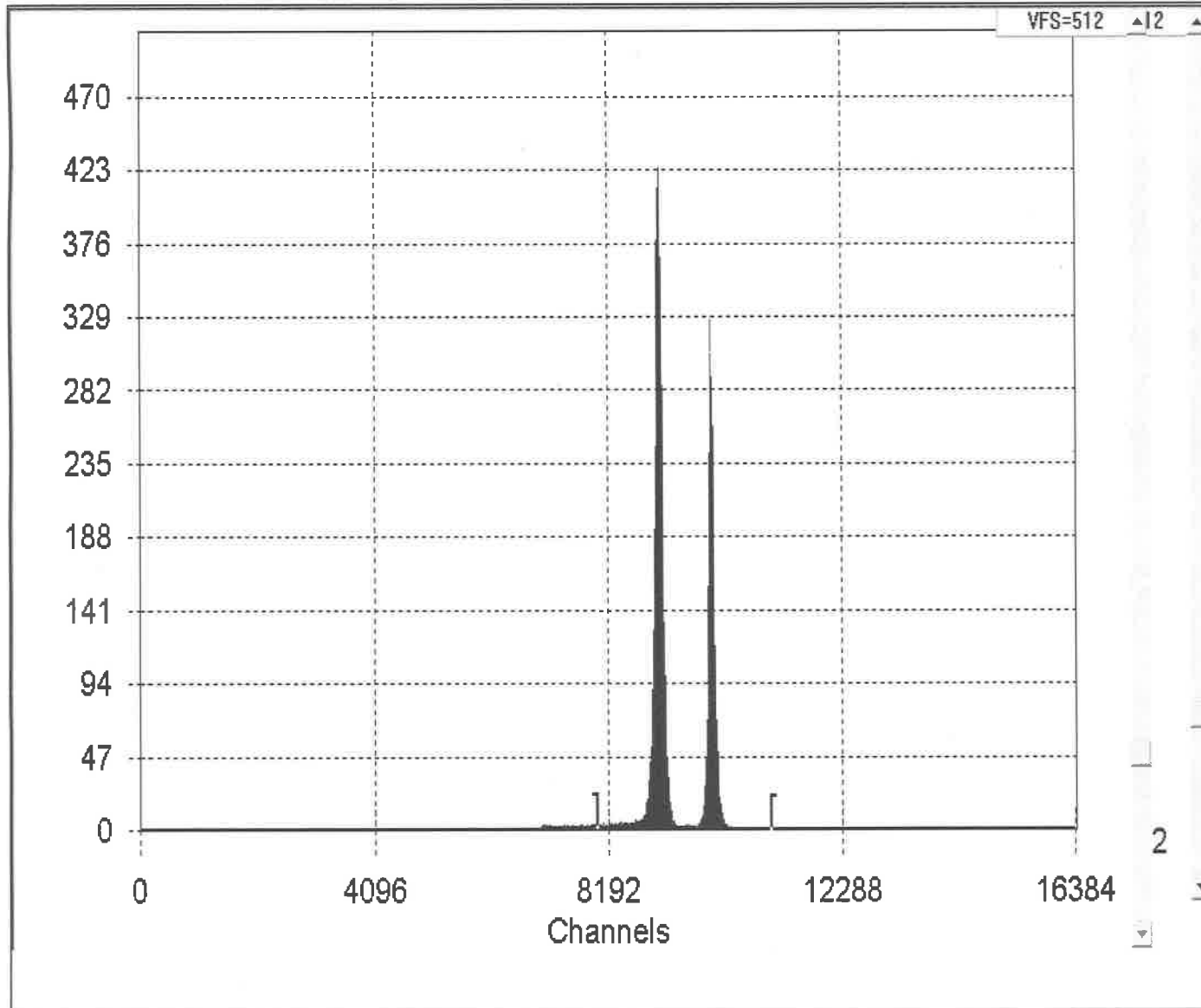
Wafer No.: **2852-14** Thickness: **290** μm

JUNCTION

DET LINE: **68.3** KeV
SYSTEM: **48.9** KeV
CAL: **47.7** KeV

OHMIC

DET LINE: **71.7** KeV
SYSTEM: **48.8** KeV
CALC: **52.5** KeV



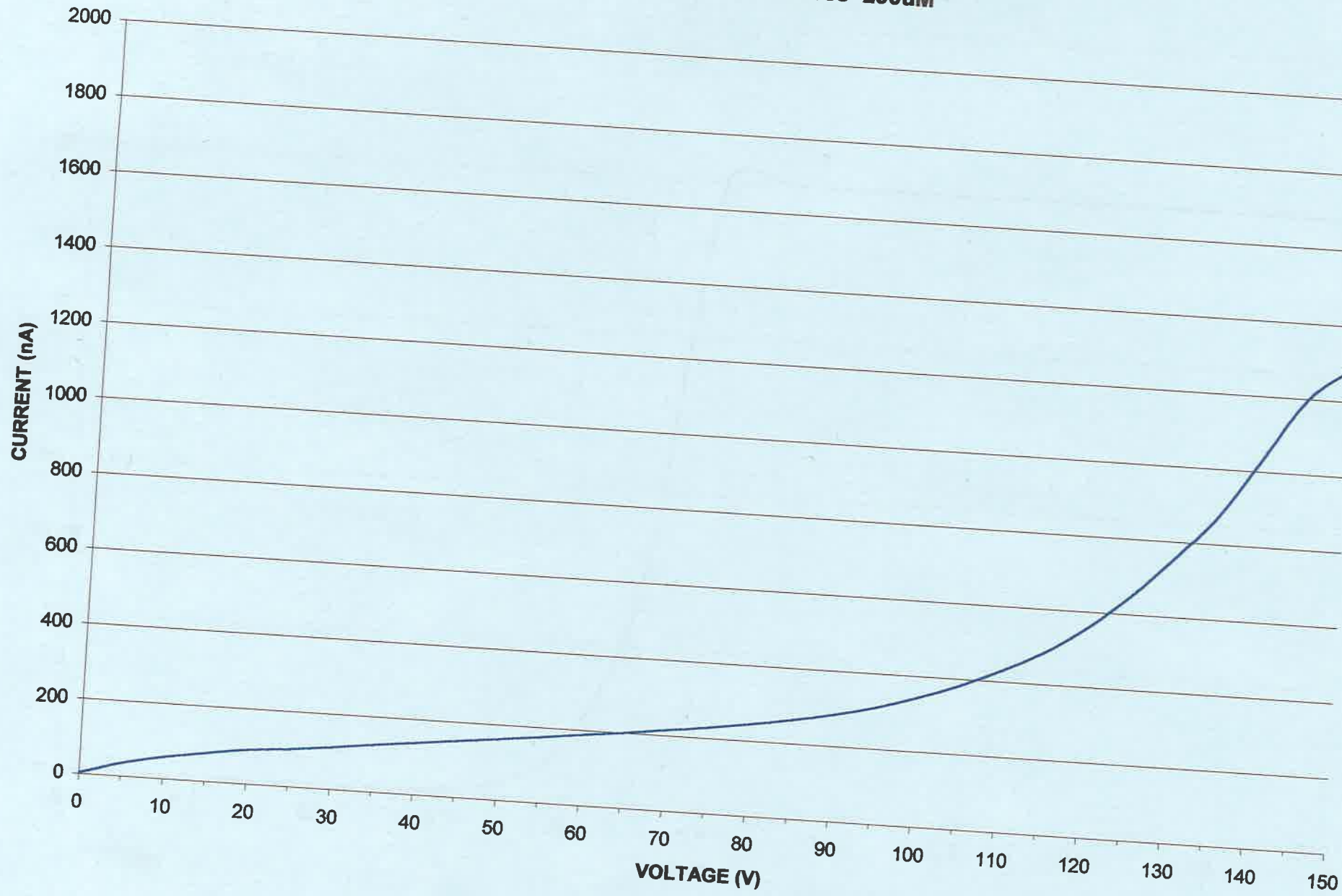
Source
Am 241

Rise Time
1

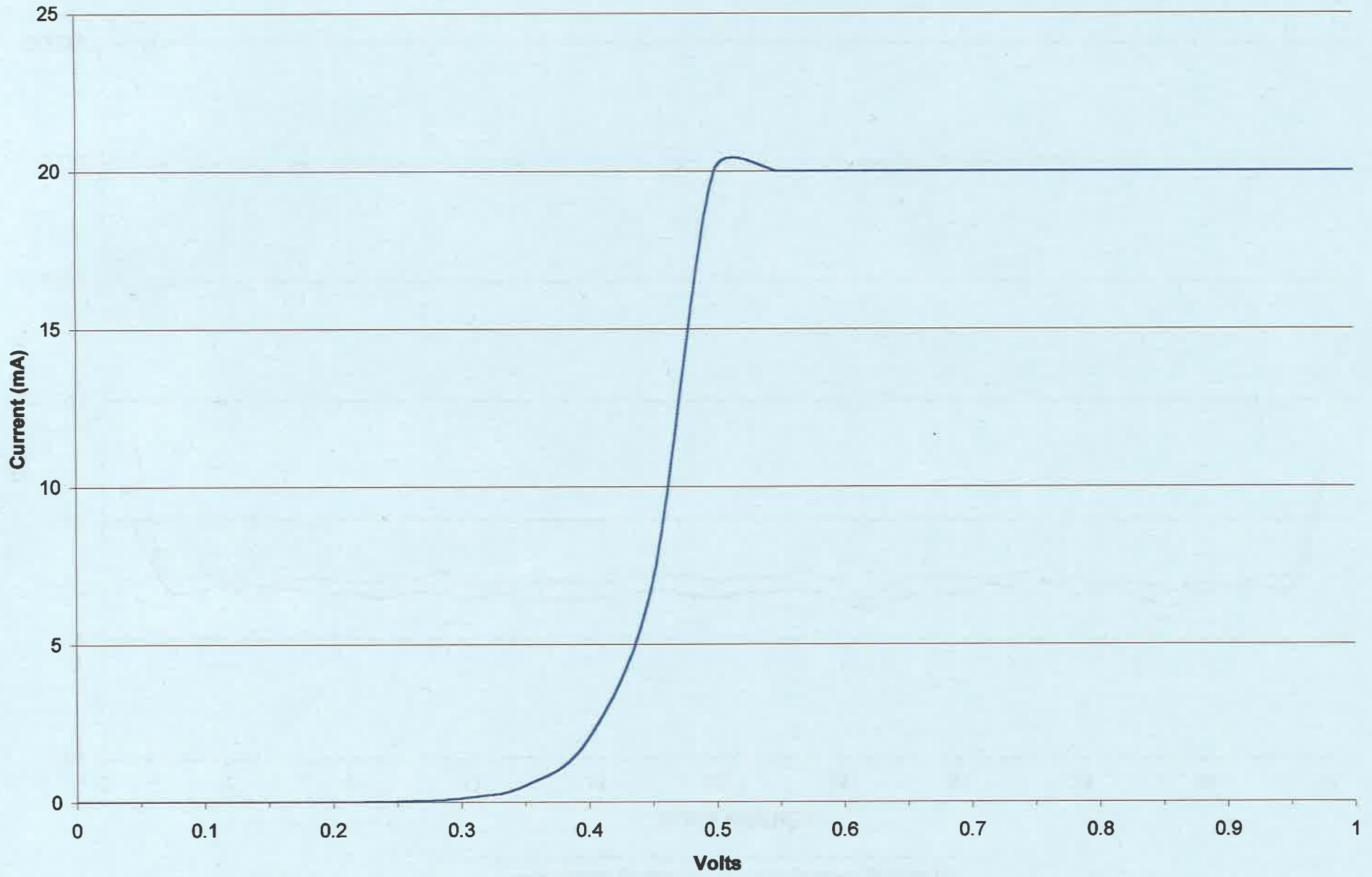
Flat Top
0

BIAS VOLTS= **60** V Leakage **140** nA

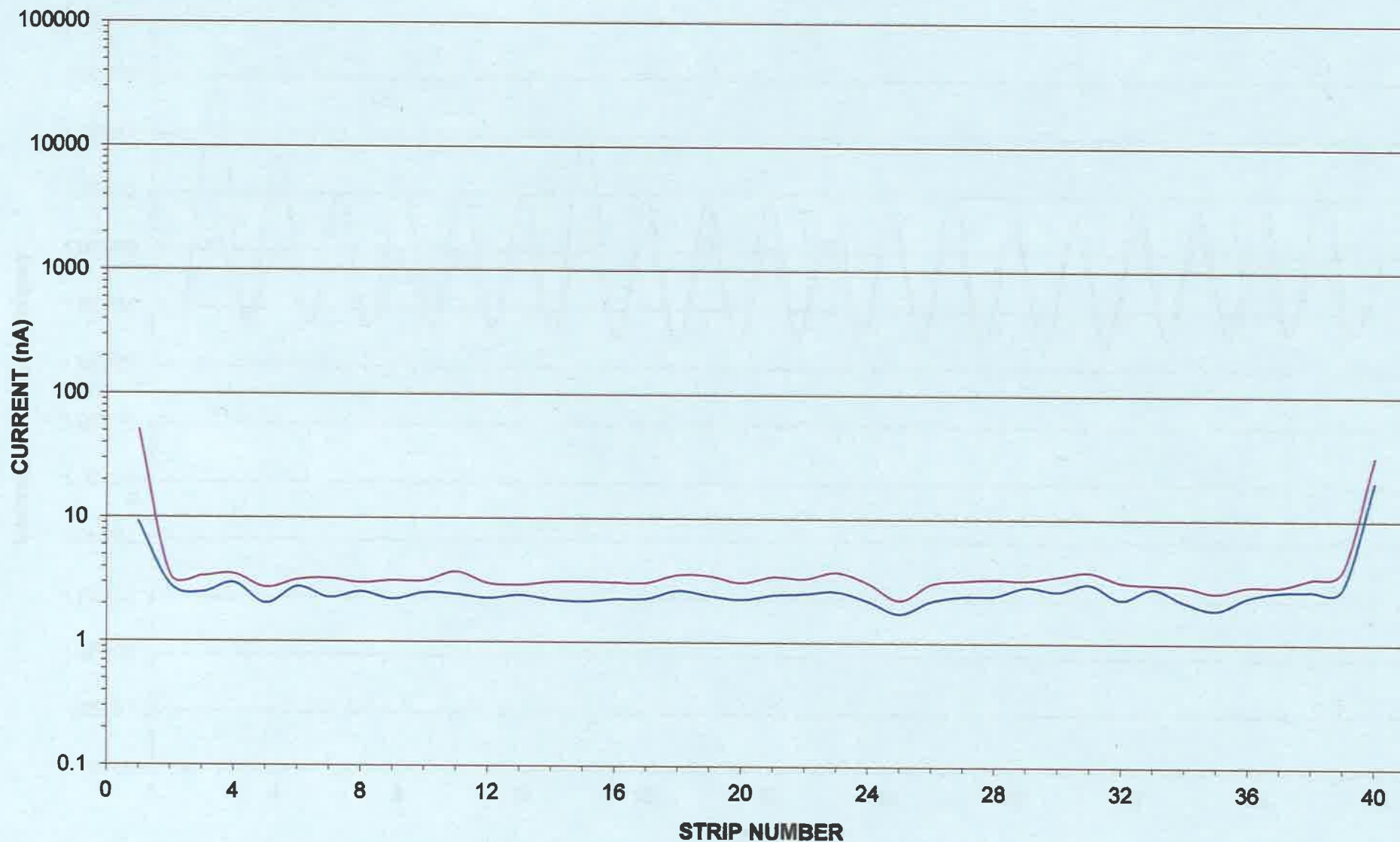
BB1-300
2852-14 Dep=30V Thickness=290uM



2852-14 ALPHA forward

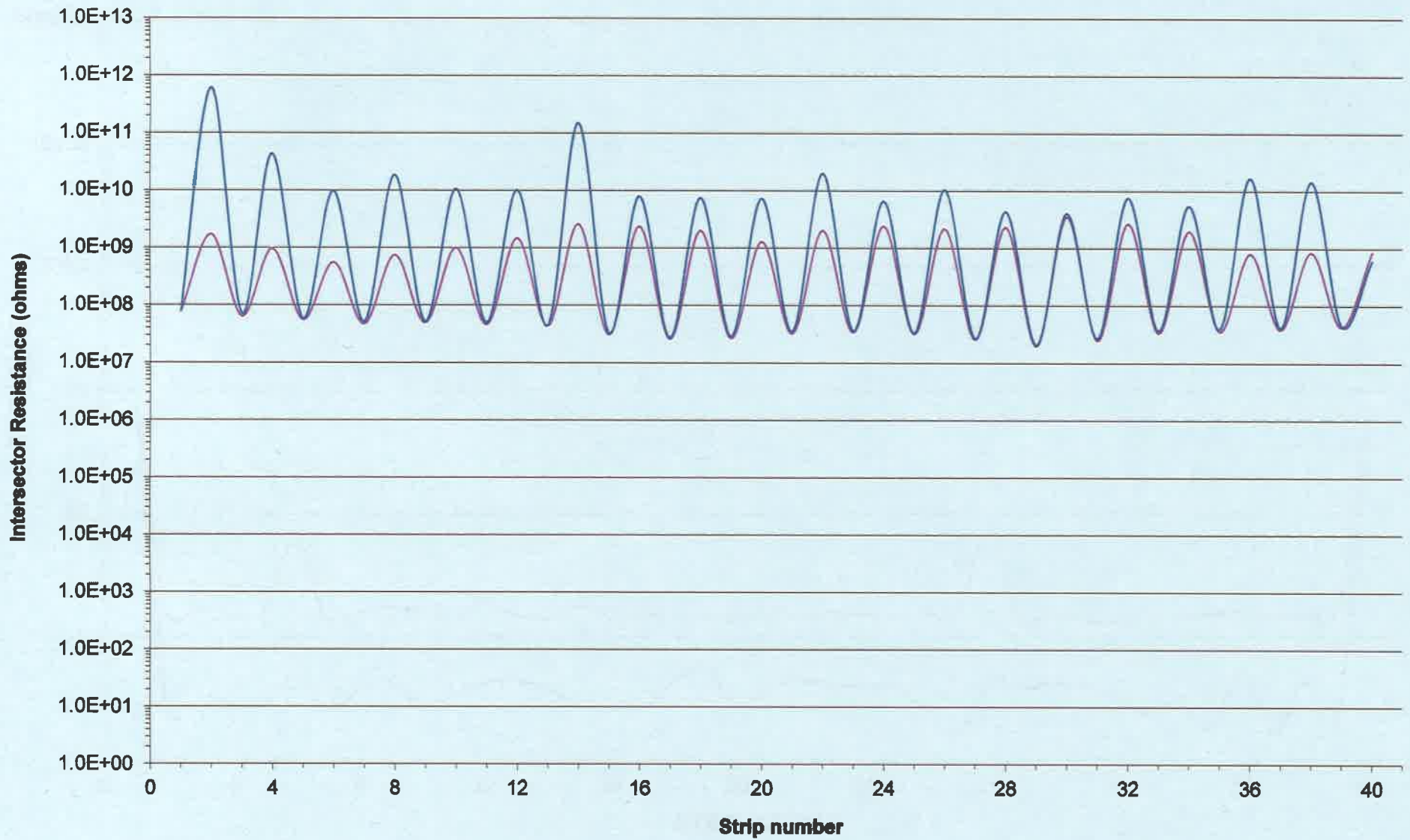


BB1-300 N-TYPE
2852-14 Junction side Dep=30V



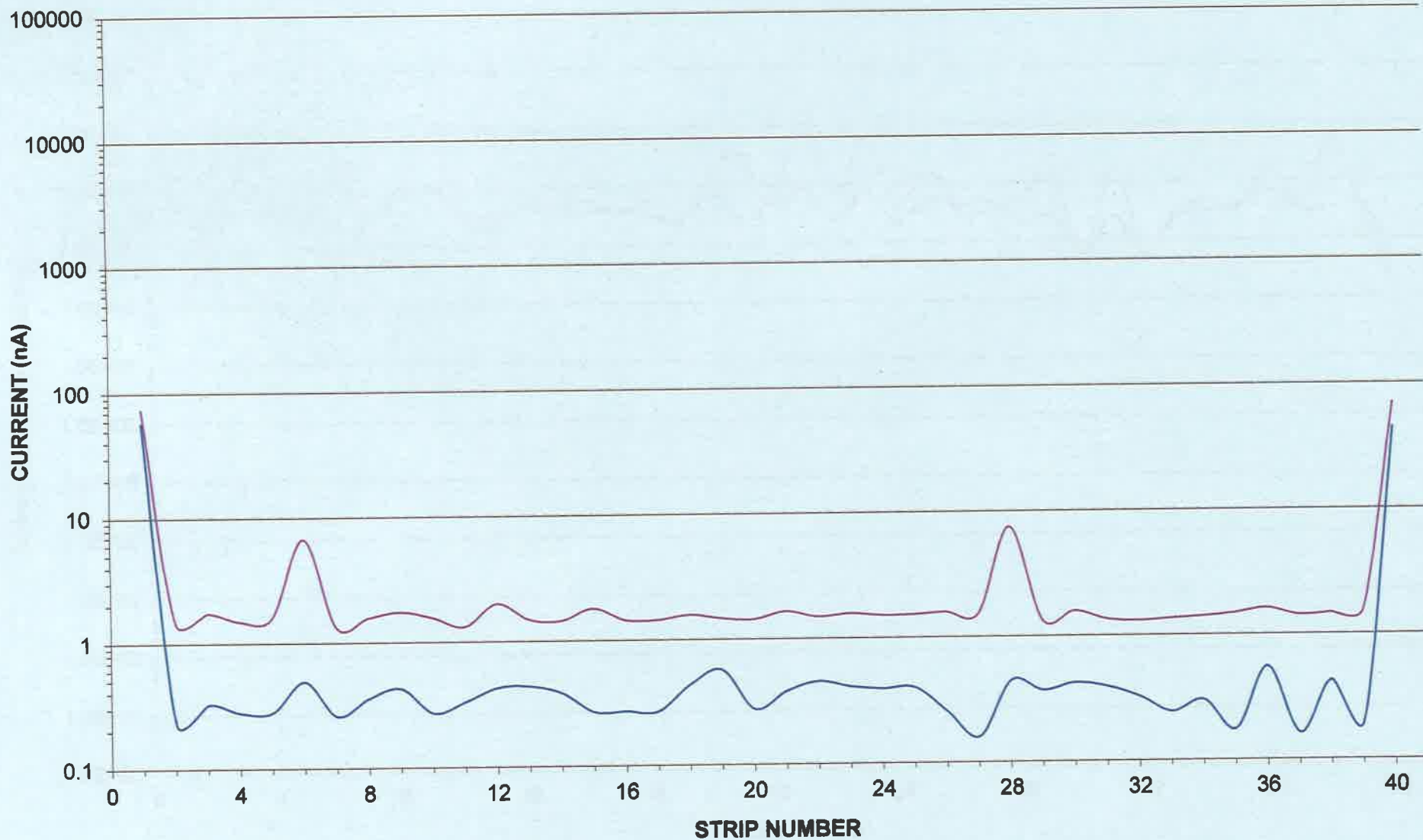
— current @ dep — current @ dep+30v

BB1-300 N-TYPE
2852-14 Junction side Dep=30V



— Inter @ Dep — Inter @ dep+30v

BB1-300 N-TYPE
2852-14 Ohmic side Dep=30V



— current @ dep — current @ dep+30v

BB1-300 N-TYPE
2852-14 Ohmic side Dep=30V

